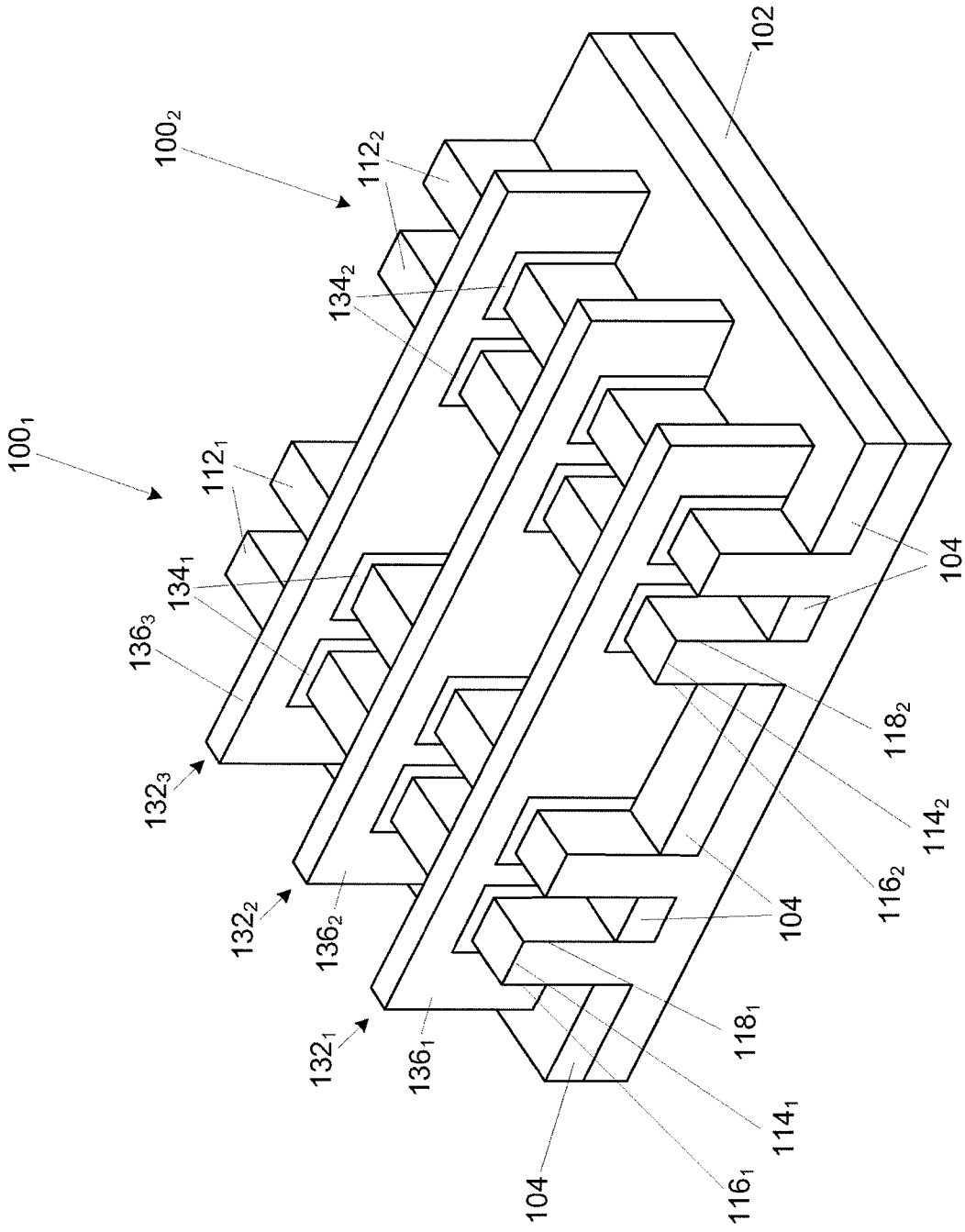

102
100_2
112_2
134_2
100_1
112_1
134_1
136_3
132_3
132_2
136_2
132_1
136_1
104
116_1
114_1
118_1
104
116_2
114_2
118_2
104

FIG. 1

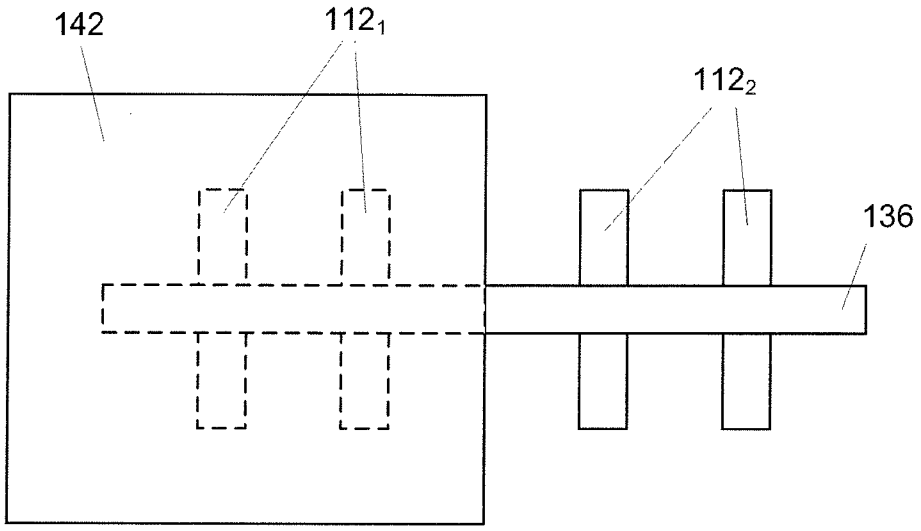


FIG. 2 (Prior Art)

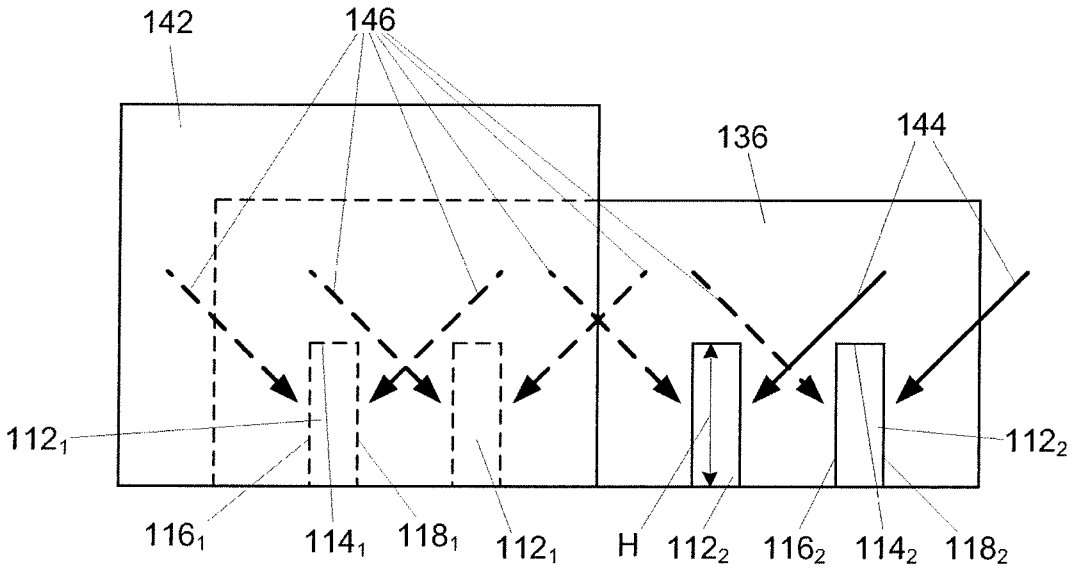


FIG. 3 (Prior Art)

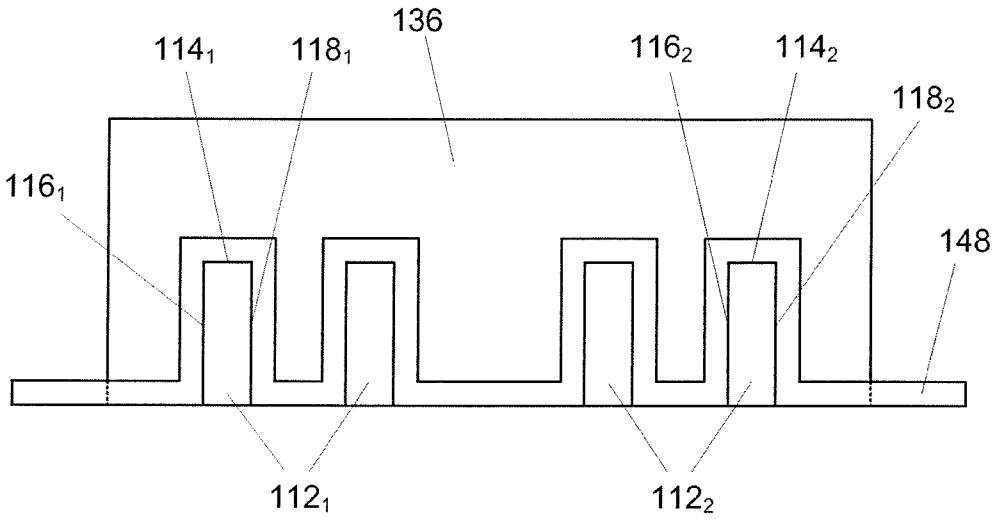

114_1
118_1
136
116_2
114_2
118_2
116_1
148
112_1
112_2

FIG. 4

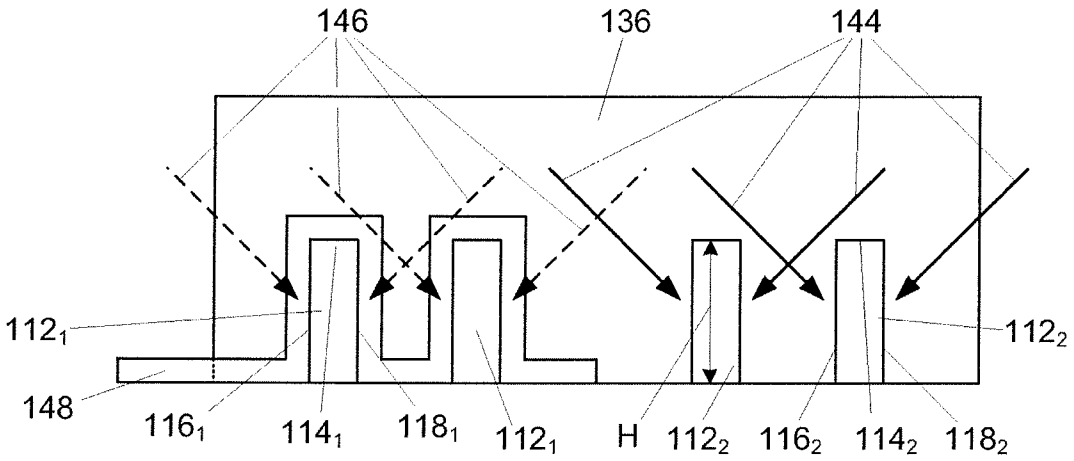

146
136
144
112_1
112_2
148
116_1
114_1
118_1
112_1
H
112_2
116_2
114_2
118_2

FIG. 5

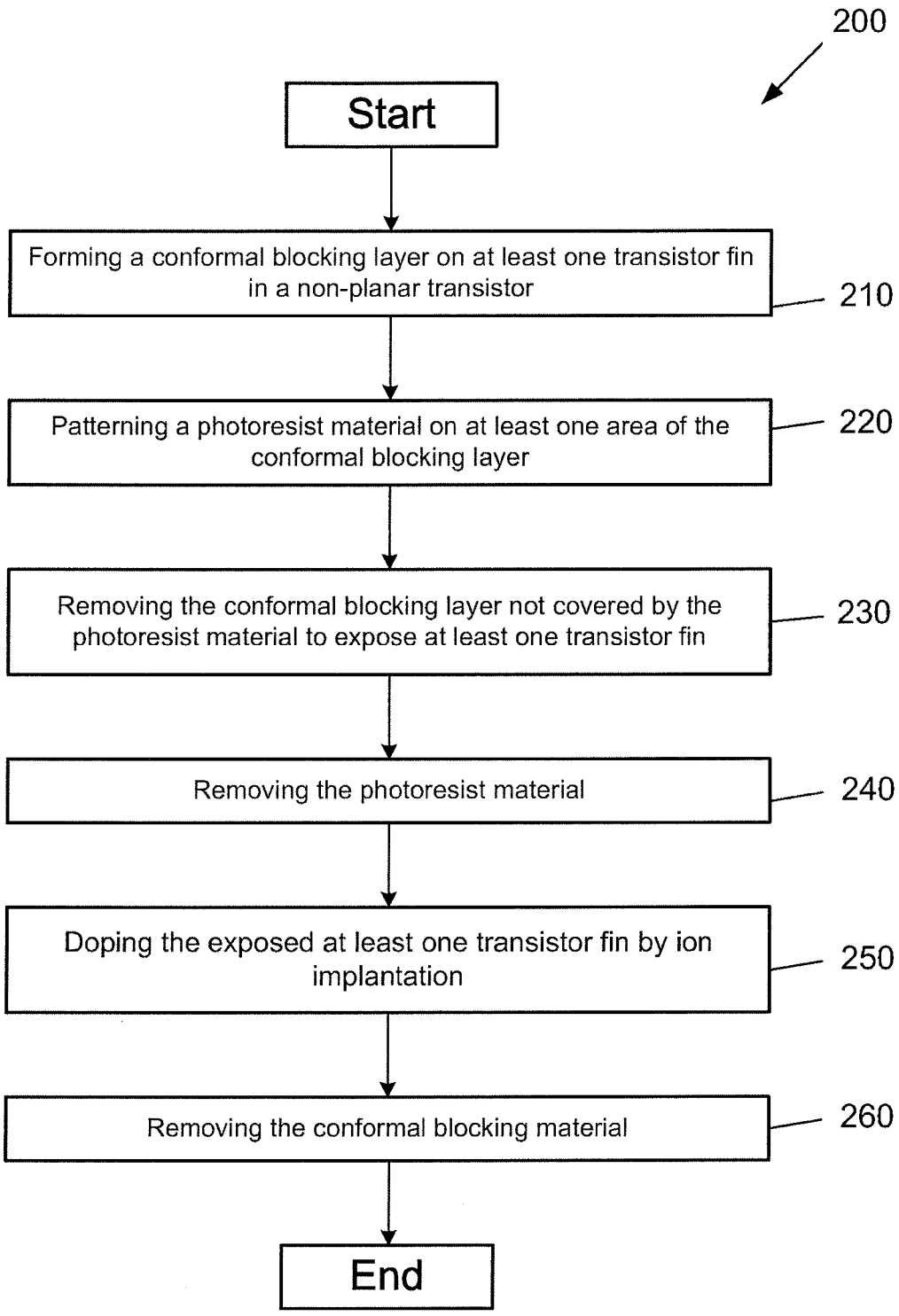

200
Start
Forming a conformal blocking layer on at least one transistor fin in a non-planar transistor
210
Patterning a photoresist material on at least one area of the conformal blocking layer
220
Removing the conformal blocking layer not covered by the photoresist material to expose at least one transistor fin
230
Removing the photoresist material
240
Doping the exposed at least one transistor fin by ion implantation
250
Removing the conformal blocking material
260
End

FIG. 6